

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

EMH1303 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- 1.8V drive
- · Protection diode in

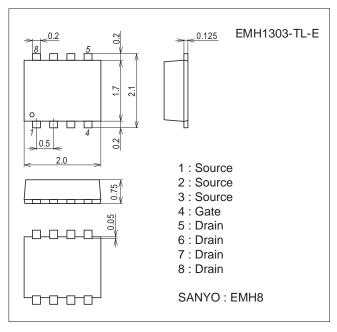
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-12	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-7	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-28	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

Package Dimensions

unit : mm (typ) 7045-001



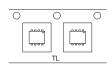
Product & Package Information

• Package : EMH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

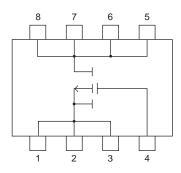
Taping Type: TL



Marking



Electrical Connection

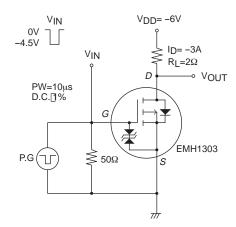


EMH1303

Electrical Characteristics at Ta=25°C

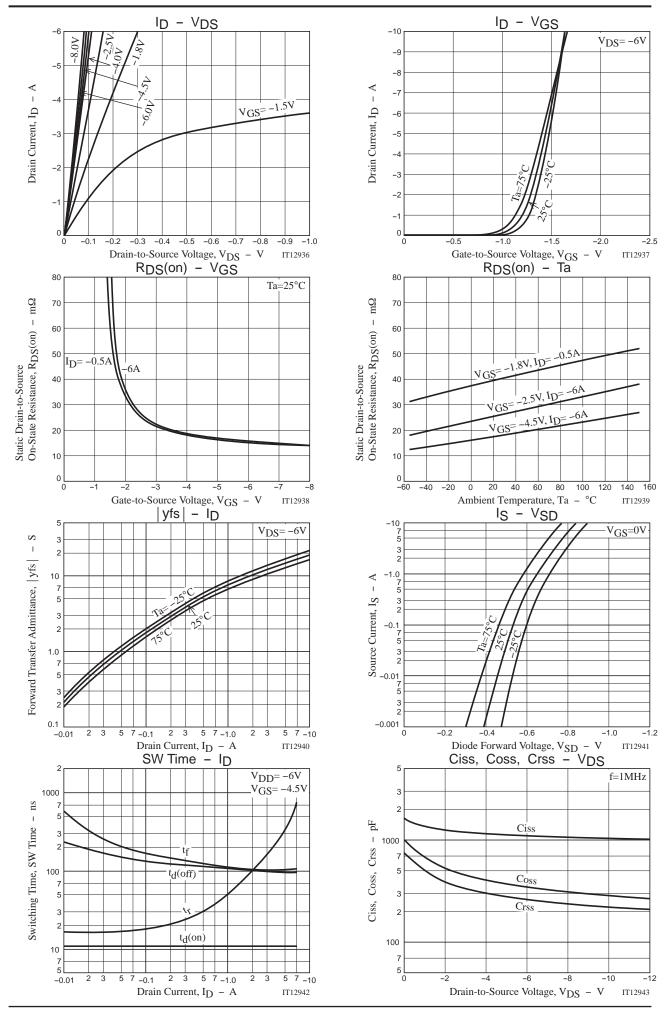
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zara Cata Valtaga Drain Current	I _{DSS} 1	V _{DS} =-8V, V _{GS} =0V			-1	μΑ	
Zero-Gate Voltage Drain Current	I _{DSS} 2	V _{DS} =-12V, V _{GS} =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	VDS=-6V, ID=-1mA	-0.4		-1.2	V	
Forward Transfer Admittance	yfs	V _{DS} =-6V, I _D =-3A	7.2	12		S	
	R _{DS} (on)1	ID=-6A, VGS=-4.5V		18	23	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-6A, V _G S=-2.5V		27	36	mΩ	
	RDS(on)3	ID=-0.5A, VGS=-1.8V		40	65	mΩ	
Input Capacitance	Ciss			1100		pF	
Output Capacitance	Coss	V _{DS} =-6V, f=1MHz		350		pF	
Reverse Transfer Capacitance	Crss			265		pF	
Turn-ON Delay Time	t _d (on)			11		ns	
Rise Time	tr	Considered Total Circuit		165		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		100		ns	
Fall Time	tf			105		ns	
Total Gate Charge	Qg			12.0		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-7A		1.9		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		2.9		nC	
Diode Forward Voltage	V _{SD}	I _S =-7A, V _G S=0V		-0.8	-1.2	V	

Switching Time Test Circuit

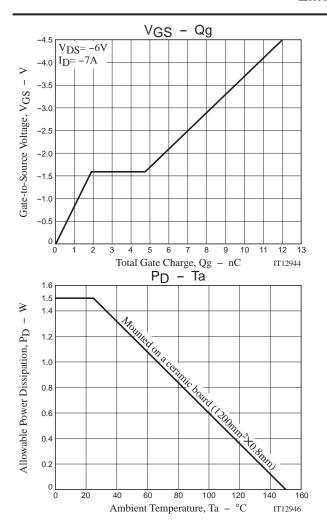


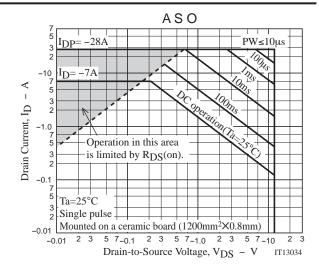
Ordering Information

Device	Package	Shipping	memo	
EMH1303-TL-E	EMH8	3,000pcs./reel	Pb Free	



EMH1303



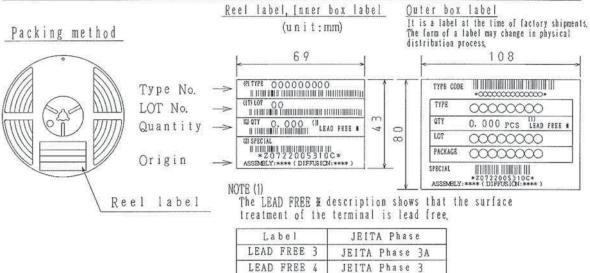


Embossed Taping Specification

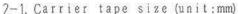
EMH1303-TL-E

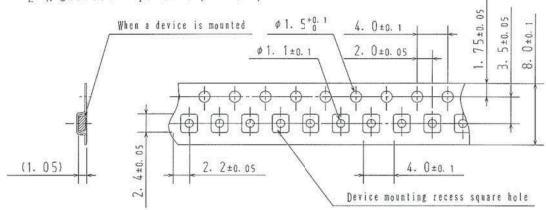
1. Packing Format

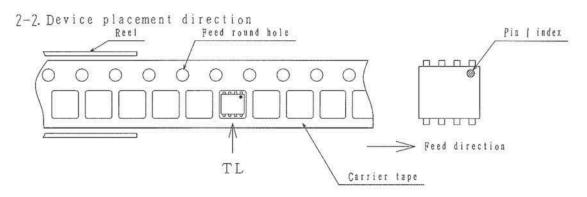
Package Name Carrier Tape Type	Carrier Tape	e Maximum Number of devices contained (pcs)			Packing format		
	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
ЕМН8	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) $440 \times 195 \times 210$	



2. Taping configuration







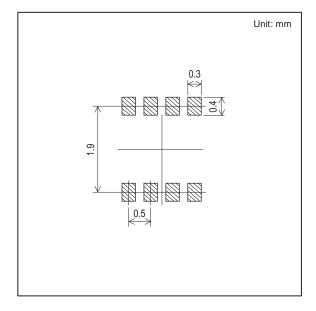
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH1303-TL-E

Mass (g) Unit 0.008 mm 2. 0±0.04 8 7 6 5 1. 125 ±0.05 1. 107 No. 1. 107 No. 1. 107 No. 1. 107 No. 1. 108 0.1 1 | Market 1 |

Land Pattern Example



Note on usage: Since the EMH1303 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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